

**AMENDMENTS TO THE SPECIFICATION**

Please replace paragraph [0033] with the following amended paragraph:

[0033] Referring now to FIG. 6C, the data line 34, the source electrode 38, and the drain electrode 40 are then provided on the gate insulating film 42. The data line 34 and the source and drain electrodes 38 and 40 are beneficially comprised of chrome (Cr) or molybdenum (Mo). The data line 4 and the source and drain electrodes 38 and 40 are formed by first depositing a metal layer (i.e., Cr or Mo) using chemical vapor deposition or sputtering. The deposited metal layer is then photolithographically patterned to produce the data line 34, the source electrode 38, and the drain electrode 40. As shown, the source and drain electrodes each have at least one protrusion that extends toward the other electrode, and the the protrusions of the source electrode is paralle to and offset from the protrusions of the drain electrode. The entirety of the protrusions of the source and drain electrodes is formed within the area of the active layer 44, as shown in Figs. 4 and 6C. After the source and drain electrodes 38 and 40 were formed, the ohmic contact layer 46 over the gate electrode 36 is patterned to expose the active layer 44. The area over the gate electrode 36 between the source and drain electrodes 38 and 40, including the protrusions, forms a channel 54 having the shape shown in FIG. 5.